

What is claimed is:

1. A light-emitting apparatus having a light-emitting device comprising:
 - a first electrode;
 - a second electrode;
 - 5 an electroluminescent film disposed between the first electrode and the second electrode;
 - a film containing fluoroplastics formed over the second electrode; and
 - an inorganic insulating film formed on the film containing fluoroplastics.
- 10 2. A light-emitting apparatus having a light-emitting device comprising:
 - a first electrode electrically connected to a TFT formed over a substrate via an insulating film;
 - a second electrode;
 - an electroluminescent film disposed between the first electrode and the second
 - 15 electrode;
 - a film containing fluoroplastics formed over the second electrode; and
 - an inorganic insulating film formed on the film containing fluoroplastics.
- 20 3. A light-emitting apparatus according to Claim 2,
 - wherein:
 - the insulating film comprises a first insulating film and a second insulating film formed on the first insulating film;
 - the first insulating film comprises a material selected from the group consisting of acrylic, polyamide, and polyimide; and

the second insulating film is a film containing fluoroplastics.

4. A light-emitting apparatus according to Claim 2, wherein the insulating film contains fluoroplastics.

5

5. A light-emitting apparatus according to Claim 1,
wherein the film containing fluoroplastics is one type of polymer selected from
polytetrafluoroethylene, tetrafluoroethylene-hexafluoropropylene copolymer,
polychlorotrifluoroethylene, tetrafluoroethylene-ethylene copolymer, polyvinyl fluoride,
10 and polyvinylidene fluoride.

6. A light-emitting apparatus according to Claim 3,
wherein:

the second insulating film is a mixed film comprising fluoroplastics and metallic
15 oxides, and

a ratio of the metallic oxides in the mixed film monotonically increases from a
portion of the mixed film distant from the first electrode to a portion of the mixed film
close to the first electrode.

20 7. A fabrication method of a light-emitting apparatus having a light-emitting device
including a first electrode, a second electrode, and an electroluminescent film disposed
between the first electrode and the second electrode, comprising the steps of:

forming a film containing fluoroplastics over the second electrode by sputtering;
treating a surface of the film containing fluoroplastics with plasma; and

forming an inorganic insulating film on the film containing fluoroplastics.

8. A fabrication method of a light-emitting apparatus having a light-emitting device including a first electrode electrically connected to a TFT formed on a substrate via an
5 insulating film, a second electrode, and an electroluminescent film disposed between the first electrode and the second electrode, comprising the steps of:

forming a film containing fluoroplastics over the second electrode by sputtering;

treating a surface of the film containing fluoroplastics with plasma; and

forming an inorganic insulating film on the film containing fluoroplastics.

10

9. A fabrication method of a light-emitting apparatus having a light-emitting device according to Claim 8,

wherein:

the insulating film comprises a first insulating film and a second insulating film
15 formed on the first insulating film;

the first insulating film comprises a material selected from the group consisting of acrylic, polyamide, and polyimide; and

the second insulating film is formed of a film containing fluoroplastics by sputtering on the first insulating film.

20

10. A fabrication method of a light-emitting apparatus having a light-emitting device according to Claim 9,

wherein a surface of the second insulating film is processed in plasma employing Ar as process gas.

11. A fabrication method of a light-emitting apparatus having a light-emitting device according to Claim 9 further comprising the steps of:

using sequentially a plurality of sputtering targets of metallic oxides,
5 fluoroplastics, or mixture of metallic oxides and fluoroplastics; and

forming the second insulating film by high-frequency sputtering with applying from 0.15 to 6.2 W per square centimeter high frequency electric power;

wherein, ratios of metallic oxides in the second insulating film is increased with deposition time.

10

12. A light-emitting apparatus according to Claim 2,

wherein the film containing fluoroplastics is one type of polymer selected from polytetrafluoroethylene, tetrafluoroethylene-hexafluoropropylene copolymer, polychlorotrifluoroethylene, tetrafluoroethylene-ethylene copolymer, polyvinyl fluoride,
15 and polyvinylidene fluoride.

13. A light-emitting apparatus according to Claim 3,

wherein the film containing fluoroplastics is one type of polymer selected from polytetrafluoroethylene, tetrafluoroethylene-hexafluoropropylene copolymer,
20 polychlorotrifluoroethylene, tetrafluoroethylene-ethylene copolymer, polyvinyl fluoride, and polyvinylidene fluoride.

14. A light-emitting apparatus according to Claim 4,

wherein the film containing fluoroplastics is one type of polymer selected from

polytetrafluoroethylene, tetrafluoroethylene-hexafluoropropylene copolymer, polychlorotrifluoroethylene, tetrafluoroethylene-ethylene copolymer, polyvinyl fluoride, and polyvinylidene fluoride.

5 15. A light-emitting apparatus according to Claim 4,

wherein:

the insulating film is a mixed film comprising fluoroplastics and metallic oxides,

and

a ratio of the metallic oxides in the mixed film monotonically increases from a
10 portion of the mixed film distant from the first electrode to a portion of the mixed film
close to the first electrode.

16. A fabrication method of a light-emitting apparatus having a light-emitting device
according to Claim 10 further comprising the steps of:

15 using sequentially a plurality of sputtering targets of metallic oxides,
fluoroplastics, or mixture of metallic oxides and fluoroplastics; and

forming the second insulating film by high-frequency sputtering with applying
from 0.15 to 6.2 W per square centimeter high frequency electric power;

wherein, ratios of metallic oxides in the second insulating film is increased with deposition
20 time.